



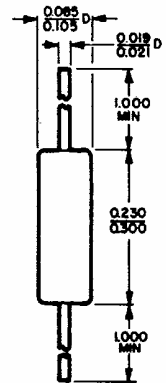
### SILICON UHF DETECTOR DIODE

The IN830 and IN830A are point contact barrier diodes used in signal detection. While Tangential Sensitivity is not specified in this instance, the diodes possess a minimum of -40 dbm up to 3 GHz.

Electrical Characteristics at  $T = 25^\circ$

Burnout CW, 375 mw  
Peak @ 1 us 15w  
Typical .3pf  $C_{jo}$

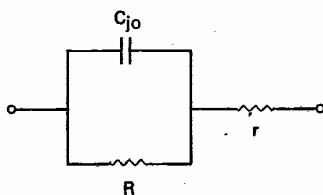
IN830 Detector rectification efficiency = 65% minimum at  $f = 100$  mc  
IN830A PIV = 5 volts minimum.



**PACKAGE  
OUTLINE**

**FIGURE 1**

DIODE Equivalent Circuit



- R = Series resistance
- r = Spreading resistance
- $C_{jo}$  = Junction Capacitance

